TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# T C 7 M E T 3 7 3 A F K

Octal D-Type Latch with 3-State Output

The TC7MET373AFK is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input (LE) and a output enable input (OE).

When the OE input is high, the eight outputs are in a high impedance state.

The input voltage are compatible with TTL output voltage.

This device may be used as a level converter for interfacing 3.3 V to 5 V system.

Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output (\*) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

\*: output in off-state

#### Features

- High speed:  $t_{pd} = 7.7$  ns (typ.) (VCC = 5 V)
- Low power dissipation:  $ICC = 4 \mu A (max) (Ta = 25^{\circ}C)$
- Compatible with TTL outputs: VIL = 0.8 V (max)
  - $V_{IH} = 2.0 V (min)$
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Low noise:  $V_{OLP} = 1.5 V (max)$
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 373 type.



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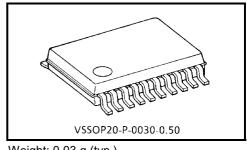
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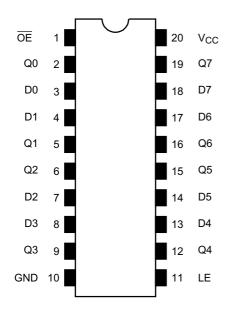
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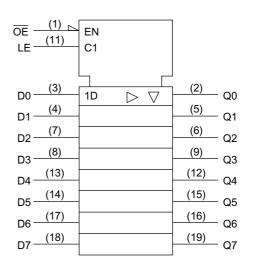
Weight: 0.03 g (typ.)

# <u>TOSHIBA</u>

# Pin Assignment (top view)



# IEC Logic Symbol



# Truth Table

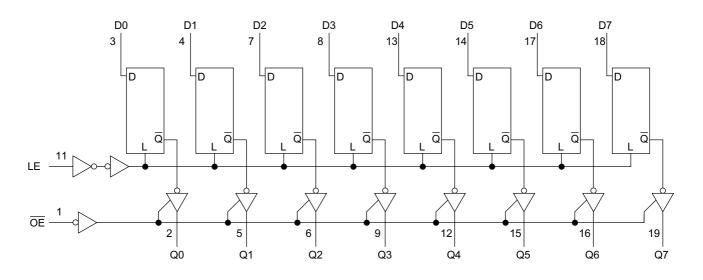
	Outputs		
ŌĒ	LE	D	Outputs
Н	Х	Х	Z
L	L	Х	Q <sub>n</sub>
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

 $\mathsf{Q}_n\!\!:\mathsf{Q}$  outputs are latched at the time when the LE input is taken to a low logic level.

# System Diagram



#### **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	Vour	-0.5~7.0 (Note1)	V
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5 (Note2)	v
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	±20 (Note3)	mA
DC output current	IOUT	±25	mA
DC V <sub>CC</sub> /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

Note1: Output in off-state

Note2: High or low state.  $\mathsf{I}_{\mathsf{OUT}}$  absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

#### **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	4.5~5.5	V	
Input voltage	V <sub>IN</sub>	0~5.5	V	
Output voltage	Maxim	0~5.5 (Note4)	V	
Output voltage	Vout	0~V <sub>CC</sub> (Note5)	v	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	0~20	ns/V	

Note4: Output in off-state

Note5: High or low state

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics		Symbol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit	
Characte	Characteristics		Symbol Test Cond		$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Onit
Input voltage	High level	VIH		_	4.5~5.5	2.0	_	_	2.0	_	V
input voltage	Low level	VIL		_	4.5~5.5		_	0.8	_	0.8	v
	High level	Veri	$V_{IN} = V_{IH}$	$I_{OH} = -50 \ \mu A$	4.5	4.4	4.5	_	4.4	_	V
	rligirlevel	V <sub>OH</sub>	or V <sub>IL</sub>	$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
Output voltage	High level	V <sub>OL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 50 \ \mu A$	4.5	_	0	0.1	—	0.1	
				$I_{OL} = 8 \text{ mA}$	4.5		—	0.36	—	0.44	
3-state output o	ff-state current	I <sub>OZ</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND		5.5	-	_	±0.25	_	±2.50	μΑ
Input leakage co	urrent	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V	√ or GND	0~5.5	_	_	±0.1		±1.0	μA
Quiescent supply current		ICC	$V_{IN} = V_{CC}$ or GND		5.5	_	—	4.0	—	40.0	μA
		ICCT	Per input: $V_{IN} = 3.4 V$ Other input: $V_{CC}$ or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage	current	I <sub>OPD</sub>	V <sub>OUT</sub> = 5.5 V		0		—	0.5	—	5.0	μA

# Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics S	Symbol	Test Condition		Ta = 25°C		Ta = −40~85°C	Unit
	Symbol	Test Condition	V <sub>CC</sub> (V)	Тур.	Limit	Limit	Unit
Minimum pulse width (LE)	t <sub>w (H)</sub> t <sub>w (L)</sub>	_	$5.0\pm0.5$	_	6.5	8.5	ns
Minimum set-up time	ts	—	$5.0\pm0.5$	_	1.5	1.5	ns
Minimum hold time	t <sub>h</sub>	_	$5.0\pm0.5$		3.5	3.5	ns

# AC Electrical Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition			-	Ta = 25°C			Ta = −40~85°C	
Characteristics Symb		Test Condition	$V_{CC}(V)$	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Unit
Propagation delay time	t <sub>pLH</sub>		5.0 ± 0.5	15	_	7.7	12.3	1.0	13.5	ns
(LE-Q)	t <sub>pHL</sub>		5.0 ± 0.5	50	_	8.5	13.3	1.0	14.5	115
Propagation delay time	t <sub>pLH</sub>		50+05	15	_	5.1	8.5	1.0	9.5	ns
(D-Q)	t <sub>pHL</sub>		5.0 ± 0.5	50	_	5.9	9.5	1.0	10.5	
3-state output enable time <sup>t</sup> pZL t <sub>pZH</sub>	t <sub>oZL</sub>	$R_L = 1 \ k\Omega$	5.0 ± 0.5	15		6.3	10.9	1.0	12.5	ns
	t <sub>pZH</sub>			50		7.1	11.9	1.0	13.5	
3-state output disable time	t <sub>pLZ</sub> t <sub>pHZ</sub>	$R_L = 1 \ k\Omega$	$5.0\pm0.5$	50		8.8	11.2	1.0	12.0	ns
Output to output skew	t <sub>osLH</sub> t <sub>osHL</sub>	(Note6)	$5.0\pm0.5$	50		_	1.0	_	1.0	ns
Input capacitance	C <sub>IN</sub>	-			_	4	10	_	10	pF
Output capacitance	C <sub>OUT</sub>	_		_	9	_	_		pF	
Power dissipation capacitance	C <sub>PD</sub>			(Note7)		25		_	_	pF

Note6: Parameter guaranteed by design.

 $t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|$ 

Note7: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per latch)

And the total  $C_{\mbox{PD}}$  when n pcs. of latch operate can be gained by the following equation:

C<sub>PD</sub> (total) = 14 + 11 • n

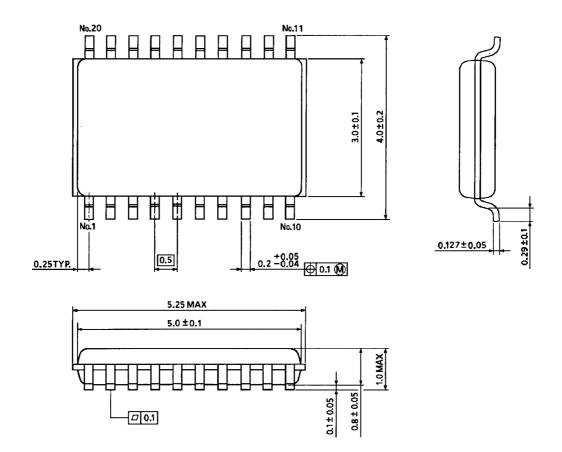
#### Noise Characteristics (Input: t<sub>r</sub> = t<sub>f</sub> = 3 ns)

Characteristics	Symbol	Test Condition	_	Ta = 25°C		Unit
Characteristics	Symbol	Test Condition	$V_{CC}(V)$	Тур.	Limit	Unit
Quiet output maximum dynamic $V_{OL}$	V <sub>OLP</sub>	$C_L = 50 \text{ pF}$	5.0	1.1	1.5	V
Quiet output minimum dynamic $V_{OL}$	V <sub>OLV</sub>	$C_L = 50 \text{ pF}$	5.0	-1.1	-1.5	V
Minimum high level dynamic input voltage $V_{IH}$	VIHD	C <sub>L</sub> = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage $V_{IL}$	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	_	0.8	V

# **Package Dimensions**

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)